# Switching Diode, High Voltage, High Temperature

#### **BASH19L Series**

#### **Features**

- 175°C T<sub>J(MAX)</sub> Rated for High Temperature, Mission Critical Applications
- NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Continuous Reverse Voltage  BASH19  BASH20  BASH21	V <sub>R</sub>	120 200 250	Vdc
Repetitive Peak Reverse Voltage BASH19 BASH20 BASH21	V <sub>RRM</sub>	120 200 250	Vdc
Continuous Forward Current	lF	200	mAdc
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	I <sub>FSM</sub>	2	Α
Repetitive Peak Forward Current (Pulse Train: T <sub>ON</sub> = 1 s, T <sub>OFF</sub> = 0.5 s)	I <sub>FRM</sub>	0.6	Α
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Electrostatic Discharge	ESD	HM < 500	V
		MM < 400	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### ON Semiconductor®

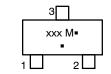
www.onsemi.com

# HIGH VOLTAGE SWITCHING DIODE



#### **MARKING DIAGRAM**





SOT-23 (TO-236) CASE 318 STYLE 8

AD7 = BASH19L
AC7 = BASH20L
AA7 = BASH21L
M = Date Code
• = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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#### **BASH19L Series**

#### THERMAL CHARACTERISTICS

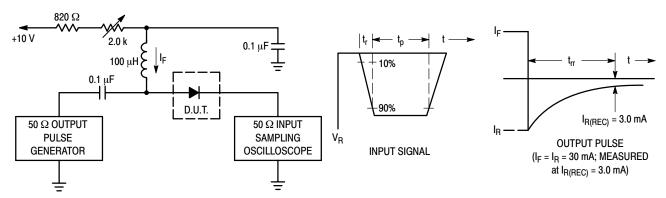
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW mW/°C
Derate above 25°C		1.0	IIIVV/ G
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	340	°C/W
Total Device Dissipation Alumina Substrate (Note 2)  T <sub>A</sub> = 25°C	P <sub>D</sub>	400	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
Reverse Voltage Leakage Current		I <sub>R</sub>			μAdc
(V <sub>R</sub> = 100 Vdc)	BASH19		-	0.1	
(V <sub>R</sub> = 150 Vdc)	BASH20		-	0.1	
(V <sub>R</sub> = 200 Vdc)	BASH21		_	0.1	
$(V_R = 100 \text{ Vdc}, T_J = 175^{\circ}\text{C})$	BASH19		_	100	
(V <sub>R</sub> = 150 Vdc, T <sub>J</sub> = 175°C)	BASH20		_	100	
(V <sub>R</sub> = 200 Vdc, T <sub>J</sub> = 175°C)	BASH21		-	100	
Reverse Breakdown Voltage		V <sub>(BR)</sub>			Vdc
(I <sub>BR</sub> = 100 μAdc)	BASH19	, ,	120	_	
(I <sub>BR</sub> = 100 μAdc)	BASH20		200	_	
(I <sub>BR</sub> = 100 μAdc)	BASH21		250	-	
Forward Voltage		V <sub>F</sub>			Vdc
(I <sub>F</sub> = 100 mAdc)			_	1.0	
(I <sub>F</sub> = 200 mAdc)			-	1.25	
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)		C <sub>D</sub>	-	5.0	pF
Reverse Recovery Time ( $I_F = I_R = 30 \text{ mAdc}$ , $I_{R(REC)} = 3.0 \text{ mA}$	Adc, R <sub>L</sub> = 100)	t <sub>rr</sub>	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0  $k\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 30 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 30 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

#### **BASH19L Series**

#### **TYPICAL CHARACTERISTICS**

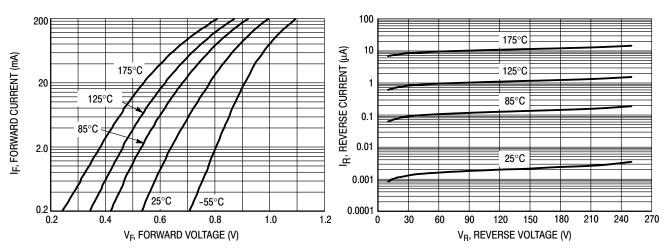


Figure 2. Forward Voltage

Figure 3. Leakage Current

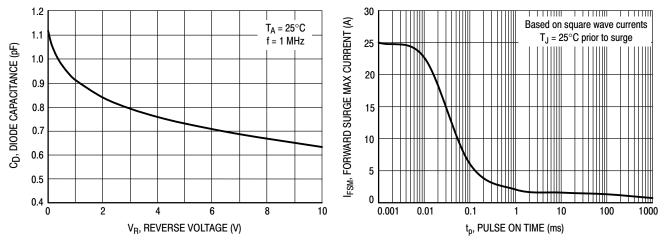


Figure 4. Capacitance

Figure 5. Forward Surge Current

#### **BASH19L Series**

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BASH19LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH19LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BASH20LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH20LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BASH21LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVBASH21LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable – release available upon request.

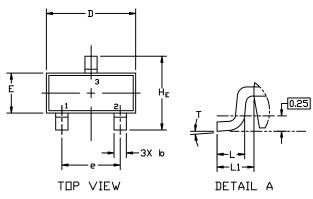


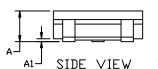


**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



#### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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